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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	Unassigned 107500268
		Filing Date	June 23, 2004
		First Named Inventor	ANDO et al.
		Art Unit	Unassigned 1733
		Examiner Name	Unassigned Hiroshiro
Sheet 1 of 1	Attorney Docket Number	92372	

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.†	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Class	SubClass	Filing Date if appropriate

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.†	Foreign Patent Document Country Code-Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Paragraphs or Figures Appear	T*
F.H.		JP 07201874	08/04/1995	NEC Corp.		Abstract
F.H.		EP 0 889 510	01/07/1999	Adachi et al.		Yes
F.H.		JP 09194294	07/29/1997	Sumitomo Sitix Corp.		Abstract
F.H.		EP 1 035 235	09/13/2000	Tamatsuka et al.		Yes

OTHER ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.†	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
F.H.		Adachi, et al.; "Reduction of Grown-In Defects by High Temperature Annealing," <i>Journal of The Electrochemical Society</i> , Vol. 147 (1), pp. 350-353, 2000.	
F.H.		Umeno et al.; "Dependence of Grown-In Defect Behavior on Oxygen Concentration in Czochralski Silicon Crystals," <i>Jpn. J. Appl. Phys.</i> , Vol. 38, Pt. 1, No. 10, pp. 5725-5730, 1999.	
F.H.		Wijaranakula et al.; "Effect of high-temperature annealing on the dissolution of the D-defects in n-type Czochralski silicon," <i>Appl. Phys. Lett.</i> , Vol. 64 (8), pp. 1030-1032, 21 February 1994.	

Examiner Signature	<i>[Signature]</i>	Date Considered	8/2/2006
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